### **Vishay Semiconductors**

## Insulated Hyperfast Rectifier Module, 280 A



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| PRIMARY CHARACTERISTICS                         |                                       |  |  |  |  |  |  |  |
|---|---------------------------------------|--|--|--|--|--|--|--|
| V <sub>R</sub>                                  | 300 V                                 |  |  |  |  |  |  |  |
| $I_{F(AV)}$ per module at $T_C = 81 \text{ °C}$ | 280 A                                 |  |  |  |  |  |  |  |
| t <sub>rr</sub>                                 | 58 ns                                 |  |  |  |  |  |  |  |
| Туре  | Modules - diode FRED Pt®              |  |  |  |  |  |  |  |
| Package   | SOT-227                               |  |  |  |  |  |  |  |
| Circuit configuration                           | Two separate diodes, parallel pin-out |  |  |  |  |  |  |  |

### **FEATURES**

- Two fully independent diodes
- · Fully insulated package
- Hyperfast, soft with reverse recovery, high operation junction temperature  $(T_{.1} max. = 175 °C)$
- Low forward voltage drop
- · Optimized for power conversion: welding and industrial SMPS applications
- · Easy to use and parallel
- Industry standard outline
- UL approved file E78996
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

### **DESCRIPTION / APPLICATIONS**

The VS-UFH280FA30 insulated modules integrate two state of the art ultrafast recovery rectifiers in the compact, industry standard SOT-227 package. The diodes structure, and its life time control, provide an ultrasoft recovery current shape, together with the best overall performance, ruggedness and reliability characteristics.

These devices are thus intended for high frequency applications in which the switching energy is designed not to be predominant portion of the total energy, such as in the output rectification stage of welding machines, SMPS, DC/DC converters. Their extremely optimized stored charge and low recovery current reduce both over dissipation in the switching elements (and snubbers) and EMI/RFI.

| ABSOLUTE MAXIMUM RATINGS                    |                      |                                 |             |       |  |  |  |
|---|----------------------|---------------------------------|-------------|-------|--|--|--|
| PARAMETER                                   | SYMBOL               | TEST CONDITIONS                 | MAX.        | UNITS |  |  |  |
| Cathode to anode voltage                    | V <sub>R</sub>       |                                 | 300         | V     |  |  |  |
| Continuous forward current per diode        | I <sub>F</sub>       | T <sub>C</sub> = 95 °C          | 160         | ٨     |  |  |  |
| Single pulse forward current per diode      | I <sub>FSM</sub>     | T <sub>C</sub> = 25 °C          | 1539        | A     |  |  |  |
| Maximum power dissipation per module        | PD                   | T <sub>C</sub> = 95 °C          | 410         | W     |  |  |  |
| RMS isolation voltage                       | VISOL                | Any terminal to case, t = 1 min | 2500        | V     |  |  |  |
| Operating junction and storage temperatures | TJ, T <sub>Stg</sub> |                                 | -55 to +175 | °C    |  |  |  |

| <b>ELECTRICAL SPECIFICATIONS PER DIODE</b> ( $T_J = 25 \text{ °C}$ unless otherwise specified) |                 |   |      |      |      |       |  |
|--|-----------------|---|------|------|------|-------|--|
| PARAMETER  | SYMBOL          | TEST CONDITIONS                                 | MIN. | TYP. | MAX. | UNITS |  |
| Cathode to anode breakdown voltage   | V <sub>BR</sub> | I <sub>R</sub> = 200 μA                         | 300  | -    | -    |       |  |
| Forward voltage  | V <sub>FM</sub> | I <sub>F</sub> = 100 A                          | -    | 1.07 | 1.27 | V     |  |
| Forward voltage  |                 | I <sub>F</sub> = 100 A, T <sub>J</sub> = 175 °C | -    | 0.82 | -    |       |  |
| Deverse leekerse overrent  | I <sub>RM</sub> | $V_{R} = V_{R}$ rated                           | -    | 0.5  | 100  | μA    |  |
| Reverse leakage current  |                 | $T_J = 175 \text{ °C}, V_R = V_R \text{ rated}$ | -    | 0.74 | -    | mA    |  |
| Junction capacitance   | CT              | V <sub>R</sub> = 300 V                          | -    | 216  | -    | pF    |  |

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1

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RoHS

COMPLIANT

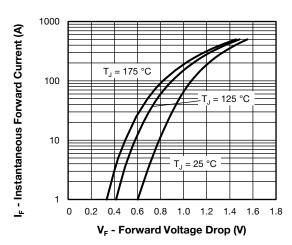


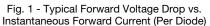
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| <b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified) |                  |                         |   |      |      |       |     |
|---|------------------|-------------------------|---|------|------|-------|-----|
| PARAMETER   | SYMBOL           | TEST CO                 | MIN.  | TYP. | MAX. | UNITS |     |
| Poverse recovery time   | +                | $T_J = 25 \ ^\circ C$   |   | -    | 58   | -     | 200 |
| Reverse recovery time   | t <sub>rr</sub>  | T <sub>J</sub> = 125 °C | I <sub>F</sub> = 50 A<br>dI <sub>F</sub> /dt = 200 A/μs<br>V <sub>R</sub> = 200 V | -    | 85   | -     | ns  |
| Deal and a second   | I <sub>RRM</sub> | T <sub>J</sub> = 25 °C  |   | -    | 4.5  | -     | A   |
| Peak recovery current   |                  | T <sub>J</sub> = 125 °C |   | -    | 10   | -     |     |
| Reverse recovery charge   | Q <sub>rr</sub>  | T <sub>J</sub> = 25 °C  |   | -    | 130  | -     | nC  |
|   |                  | T <sub>J</sub> = 125 °C |   | -    | 429  | -     |     |

| THERMAL - MECHANICAL SPECIFICATIONS     |                   |                       |         |      |            |             |  |
|---|-------------------|-----------------------|---------|------|------------|-------------|--|
| PARAMETER                               | SYMBOL            | TEST CONDITIONS       | MIN.    | TYP. | MAX.       | UNITS       |  |
| Junction-to-case, single leg conducting | Р                 |                       | -       | -    | 0.39       |             |  |
| Junction-to-case, both leg conducting   | R <sub>thJC</sub> |                       | -       | -    | 0.195      | °C/W        |  |
| Case-to-heatsink                        | R <sub>thCS</sub> | Flat, greased surface | -       | 0.1  | -          |             |  |
| Weight                                  |                   |                       | -       | 30   | -          | g           |  |
| Mounting torque                         |                   | Torque to terminal    | -       | -    | 1.1 (9.7)  | Nm (lbf.in) |  |
| Mounting torque                         |                   | Torque to heatsink    | -       | -    | 1.8 (15.9) | Nm (lbf.in) |  |
| Case style                              |                   |                       | SOT-227 |      |            |             |  |





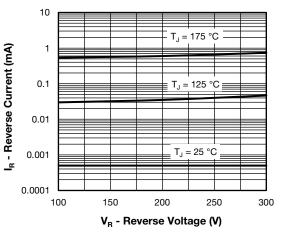
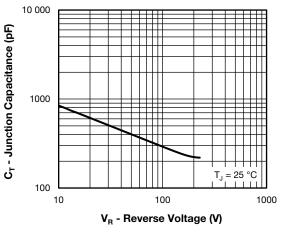


Fig. 2 - Typical Reverse Current vs. Reverse Voltage (Per Diode)





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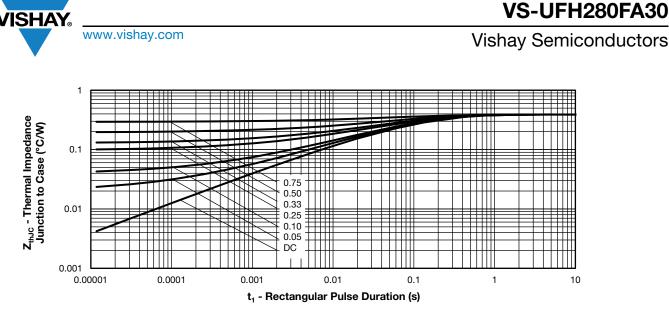


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics (Per Diode)

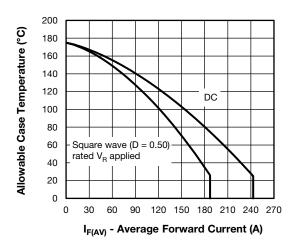


Fig. 5 - Maximum Current Rating Capability (Per Diode)

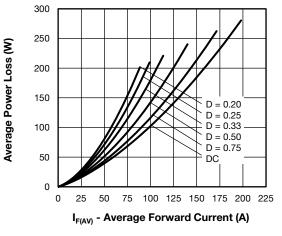
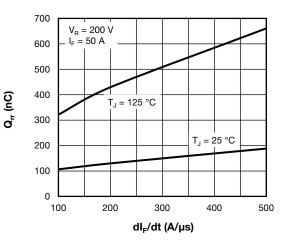


Fig. 6 - Forward Power Loss Characteristics (Per Diode)



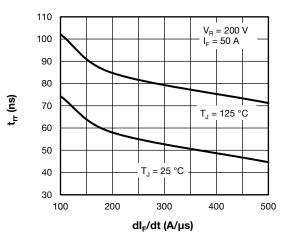


Fig. 7 - Typical Reverse Recovery Charge vs. dl<sub>F</sub>/dt (Per Diode)

Fig. 8 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt (Per Diode)

## VS-UFH280FA30

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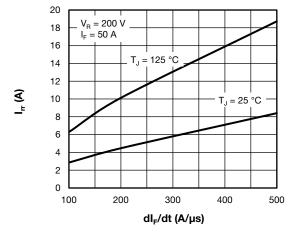


Fig. 9 - Typical Reverse Recovery Current vs. dl<sub>F</sub>/dt (Per Diode)

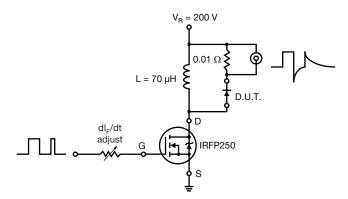
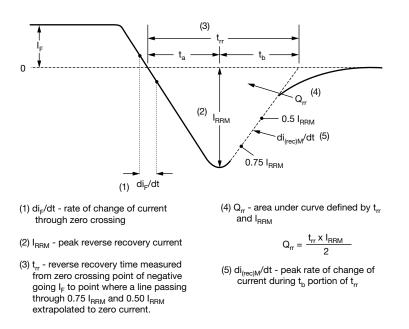
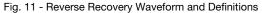


Fig. 10 - Reverse Recovery Parameter Test Circuit









### **ORDERING INFORMATION TABLE**

| Device code | vs- | UF   | н         | 280       | F                     | Α        | 30       |
|-------------|-----|------|-----------|-----------|-----------------------|----------|----------|
|             |     | 2    | 3         | 4         | 5                     | 6        | 7        |
|             | 1 - | Visł | nay Sen   | niconduc  | ctors pro             | oduct    |          |
|             | 2 - | Ultr | a fast re | ctifier   |                       |          |          |
|             | 3 - | Нур  | er fast l | FRED P    | t <sup>®</sup> diffus | ed       |          |
|             | 4 - | Cur  | rent rati | ng (280   | = 280 A               | A)       |          |
|             | 5 - | Circ | uit conf  | iguratior | n (two s              | eparate  | diodes   |
|             | 6 - | Pac  | kage in   | dicator ( | SOT-22                | 27 stand | lard ins |
|             | 7 - | Volt | age rati  | ng (30 =  | = 300 V)              | )        |          |

| CIRCUIT CONFI                            | GURATION                      |                 |
|--|-------------------------------|-----------------|
| CIRCUIT                                  | CIRCUIT<br>CONFIGURATION CODE | CIRCUIT DRAWING |
| Two separate diodes,<br>parallel pin-out | F                             | Lead Assignment |

| LINKS TO RELATED DOCUMENTS |                          |  |  |  |  |
|----------------------------|--------------------------|--|--|--|--|
| Dimensions                 | www.vishay.com/doc?95423 |  |  |  |  |
| Packaging information      | www.vishay.com/doc?95425 |  |  |  |  |

**Vishay Semiconductors** 



SOT-227 Generation 2

### **DIMENSIONS** in millimeters (inches)



#### Note

• Controlling dimension: millimeter



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1